NPN Silicon Phototransistor

OP599 Series



Features:

- Dark blue injection-molded plastic package
- · Variety of sensitivity ranges
- T-1¾ package style with TO-18 base
- Excellent optical lens surface
- Excellent chip placement



Description:

Each device in this series consists of a NPN silicon phototransistor mounted in a dark blue plastic injection molded shell package, with a narrow receiving angle that provides excellent on-axis coupling and optical/mechanical axis alignment. The shell also provides excellent optical lens surface, control of chip placement and consistency of the outside package dimensions.

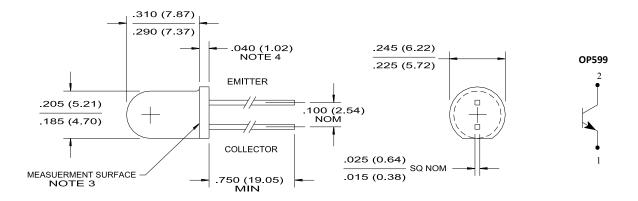
The OP599 series sensors are 100% production tested for close correlation with OPTEK GaAIAs emitters.

Please refer to Application Bulletins 208 and 210 for additional design information and reliability (degradation) data.

Applications:

- · Applications requiring a narrow receiving angle
- Applications that are space-limited

	Orderin	g Information	
Part Number	Sensor	Viewing Angle	Lead Length
OP599A			
OP599B	Transistor	20°	0.75"
OP599C			



DIMENSIONS ARE IN: [MILLIMETERS] INCHES



Pin#	Sensor
1	Emitter
2	Collector

CONTAINS POLYSULFONE

To avoid stress cracking, we suggest using ND Industries' **Vibra-Tite** for thread-locking. **Vibra-Tite** evaporates fast without causing structural failure in OPTEK'S molded plastics.

OPTEK Technology, Inc.

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Electrical Specifications

Absolute Maximum Ratings (T _A = 25° C unless otherwise noted)				
Storage and Operating Temperature Range	-40° C to +100° C			
Collector-Emitter Voltage	30 V			
Emitter-Collector Voltage	5 V			
Continuous Collector Current	50 mA			
Lead Soldering Temperature [1/16 inch (1.6 mm) from case for 5 seconds with soldering iron]	260° C ⁽¹⁾			
Power Dissipation	100 mW ⁽²⁾			

SYMBOL	PARAMETER	MIN	TYP	MAX	UNITS	TEST CONDITIONS	
	On-State Collector Current						
	OP599A	2.35	-	3.85	mA	G = N = t = (2)	
I _{C(ON)}	OP599B	1.20	-	1.95	mA	See Note (3).	
	OP599C	0.40	-	-	mA		
I _{CEO}	Collector-Dark Current	-	-	100	nA	V _{CE} = 10.0 V, E _E = 0	
V _{(BR)CEO}	Collector-Emitter Breakdown Voltage	30	-	-	V	Ι _C = 100 μΑ	
V _{(BR)ECO}	Emitter-Collector Breakdown Voltage	5.0	-	-	V	Ι _Ε = 100 μΑ	
V _{CE(SAT)}	Collector-Emitter Saturation Voltage	-	-	0.40	V	$I_C = 100 \mu A, E_E = 0.25 \text{ mW/cm}^2$	

Notes:

- 1. RMA flux is recommended. Duration can be extended to 10 seconds maximum when flow soldering. A maximum 20 grams force may be applied to the leads when soldering.
- 2. Derate linearly 1.33 mW/° C above 25° C.
- 3. $V_{CE} = 5 \text{ V}$. Light source is an unfiltered GaAlAs emitting diode operating at peak emission wavelength of 890 nm and $E_{E(APT)}$ of 0.25 mW/cm².
- 4. This dimension is held to within ±0.005" on the flange edge and may vary up to ±0.020" in the area of the leads.

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Performance

Typical Spectral Response

